

Title (en)
METHOD OF PRODUCING AN MOS TRANSISTOR

Title (de)
VERFAHREN ZUR HERSTELLUNG EINES MOS-TRANSISTORS

Title (fr)
PROCEDE DE FABRICATION D'UN TRANSISTOR MOS

Publication
EP 0839386 B1 20001004 (DE)

Application
EP 96920735 A 19960702

Priority
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• DE 19526184 A 19950718

Abstract (en)
[origin: WO9704480A1] When an MOS transistor is produced in a substrate (1), source/drain regions (9) and a doped gate electrode (10) are formed simultaneously by out-diffusion out of a doped layer (8), the distribution of the dopant in the source/drain regions (9) being adjusted by a permeable diffusion barrier (7) on the surface of the source/drain regions (9). Furthermore, a dopant barrier (3') can be provided, which prevents dopant passing out of the gate electrode (10) and into the semiconductor substrate (1).

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IPC 8 full level
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